



3D Modeling of Superluminescent Light-Emitting Diodes



Outline

- Introduction
- Theoretical models based on Green's function theory
- Results and comparison with experiments
- Summary

Introduction

- SLED is a light source with properties between those of LED and LD, high power, broad band and good directionality
- Used in communication, sensing, and medical instruments.
- SLED spectrum is sensitive to carrier distribution inside MQWs.
- Accurate modeling tool is useful for the design

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- LED: spontaneous emission, broad band, low power
- LD: stimulated emission, narrow band, high power, high directionality
- SLED: amplified spontaneous emission, broad band, high power, high directionality

Theoretical Models

- So far, two types of model in literatures
 - 1-D wave equation along \mathbf{z} (propagation) direction. Neglects the carrier transport on transverse plane and lateral optical confinement.
 - 2-D carrier transport model, assumes uniform carrier distribution in \mathbf{z} , and neglects spatial hole burning (SHB).
- Our approach combines 3-D carrier transport, 2-D transverse optical profile and 1-D optics along \mathbf{z}

System of equations

3D drift-diffusion equation:

$$\nabla \cdot \epsilon \nabla \phi + q(n - p - N_D^+ + N_A^-) = 0$$

$$\nabla \cdot J_n = U + q \frac{\partial n}{\partial t}$$

$$-\nabla \cdot J_p = U + q \frac{\partial p}{\partial t}$$

Separating 3D optical field:

$$E_\omega(x, y, z) = \sum_n E(z)_\omega \psi_n(x, y)$$


Transverse Helmholtz equation:

$$\Delta_T \psi_n(x, y) + \frac{\omega^2}{c^2} \epsilon \psi_n(x, y) = k_n^2 \psi_n(x, y)$$

Green's function theory

1-D inhomogeneous
Helmholtz equation

Spontaneous
noise

$$\left[\frac{\partial^2}{\partial z^2} + k_n^2(z) \right] E_\omega(z) = f_\omega(z)$$


Green's function is a solution of

$$\left[\frac{\partial^2}{\partial z^2} + k_n^2(z) \right] g(z, z_s) = \delta(z - z_s)$$

Contribution of point source at
 z_s to the field at z

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Solution

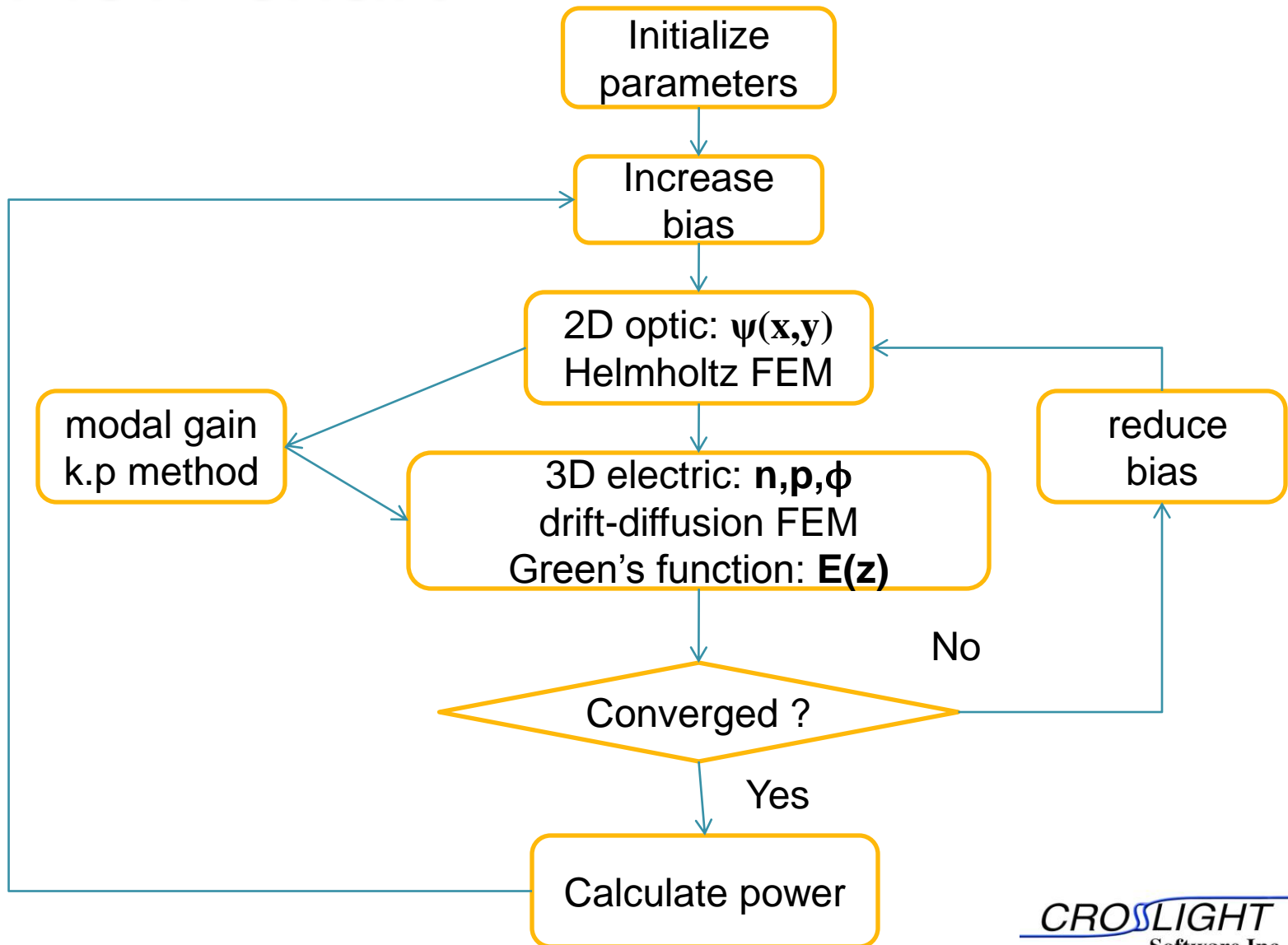
$$E_{\omega}(z) = \int_0^L g(z, z_s) f_{\omega}(z_s) dz_s$$

Spontaneous noise power

$$\langle S_{\omega}(z) \rangle = \int_{-\infty}^{\infty} \langle E_{\omega}(z) E_{\omega'}^*(z) \rangle d\omega'$$

Z.Q. Li and Simon Li, IEEE JQE, vol.46, p.454, 2010
R. Loudon et al., J. Lightw. Tech., vol.23, 2491, 2005

Flow-chart



Test device structure

QW1: 15nm

$\text{In}_{53}\text{Ga}_{47}\text{As}$

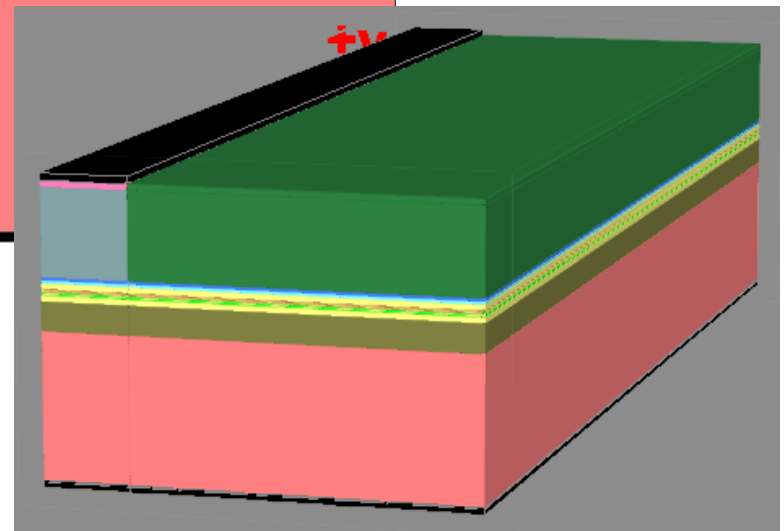
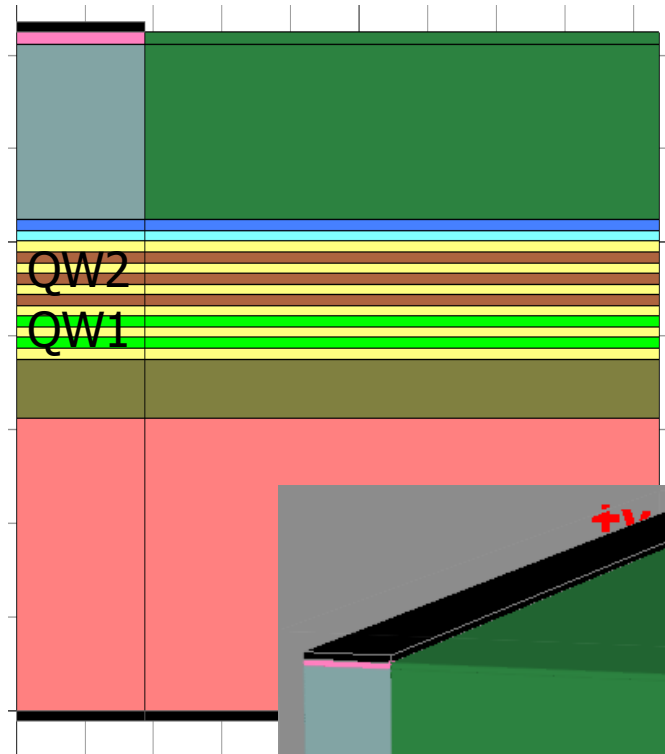
QW2: 6nm

$\text{In}_{67}\text{Ga}_{33}\text{As}_{72}\text{P}_{28}$

Barrier: 15nm

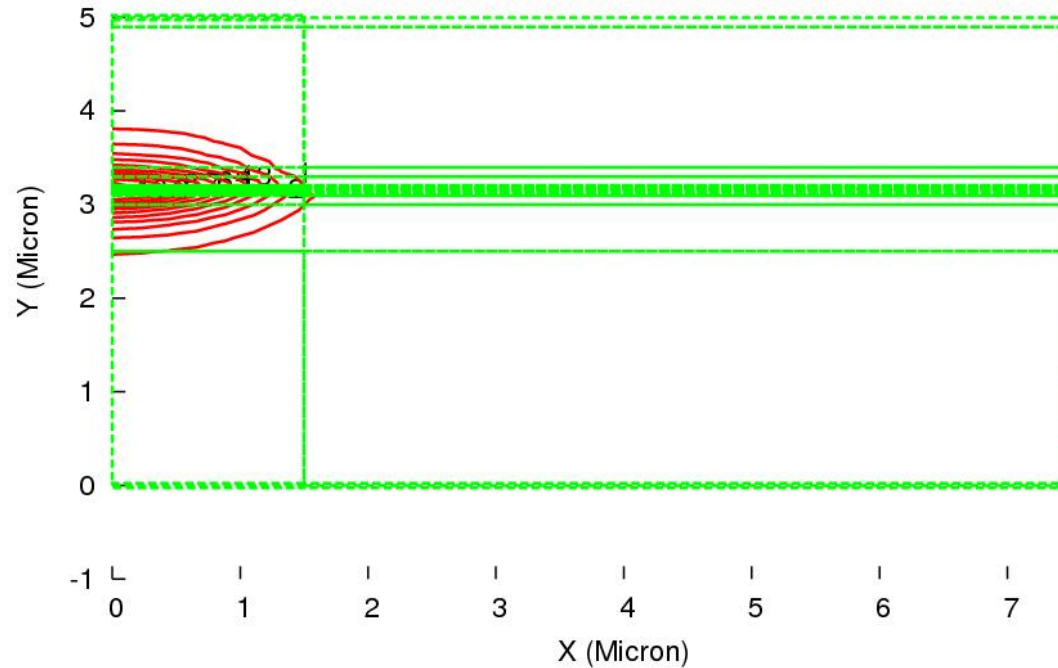
$\text{In}_{86}\text{Ga}_{14}\text{As}_{30}\text{P}_{70}$

Length: $300\mu\text{m}$



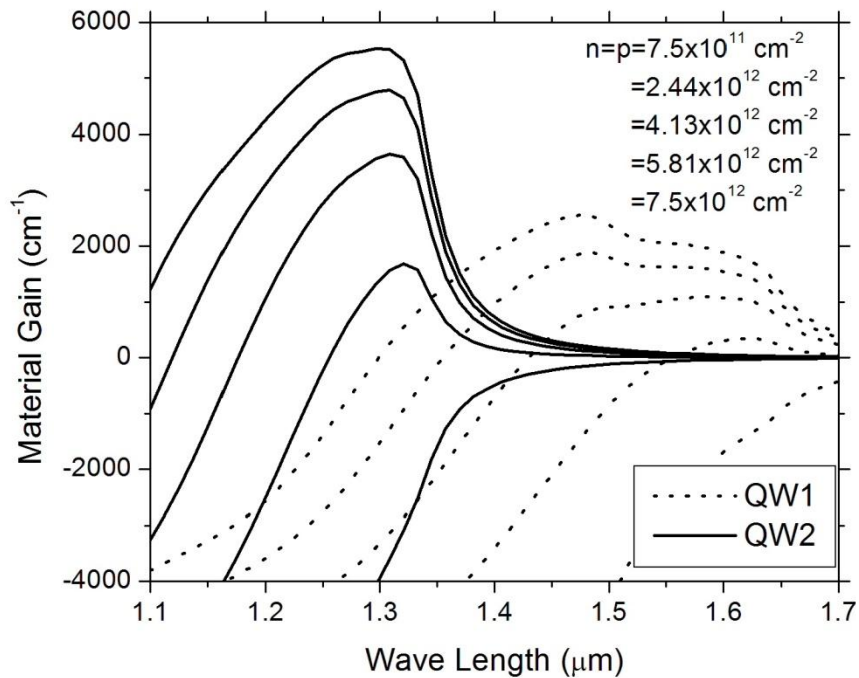
C.F. Lin, et al. IEEE Photon.
Tech. Lett. Vol16, p1441,2004

Lateral mode profile

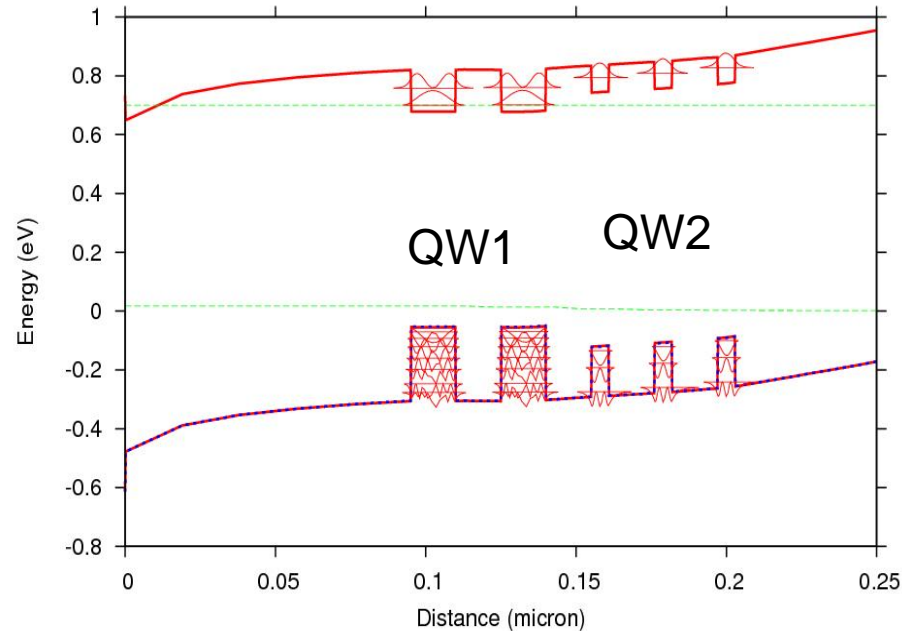


Multiple lateral modes
can be included

Material gains of QW

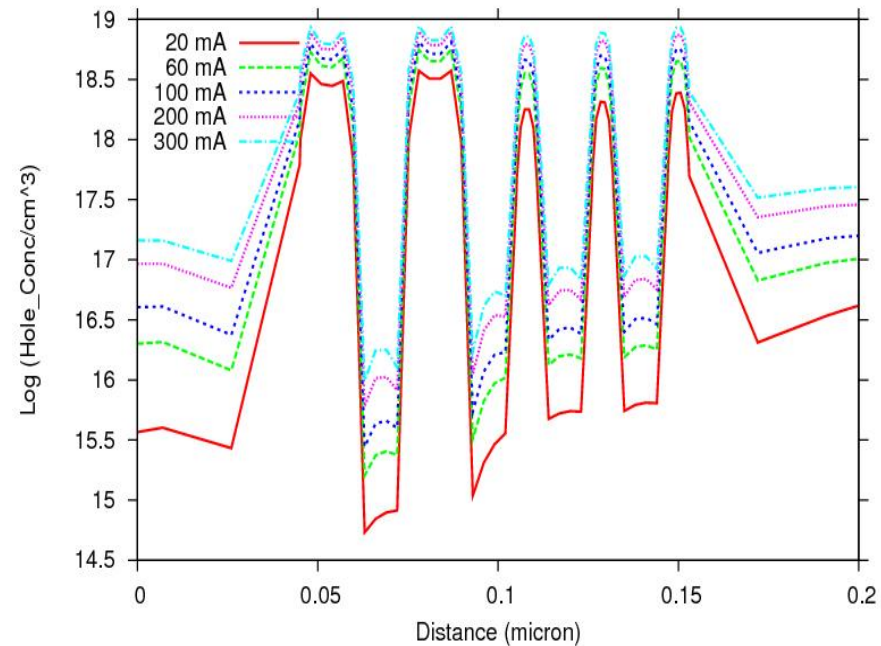
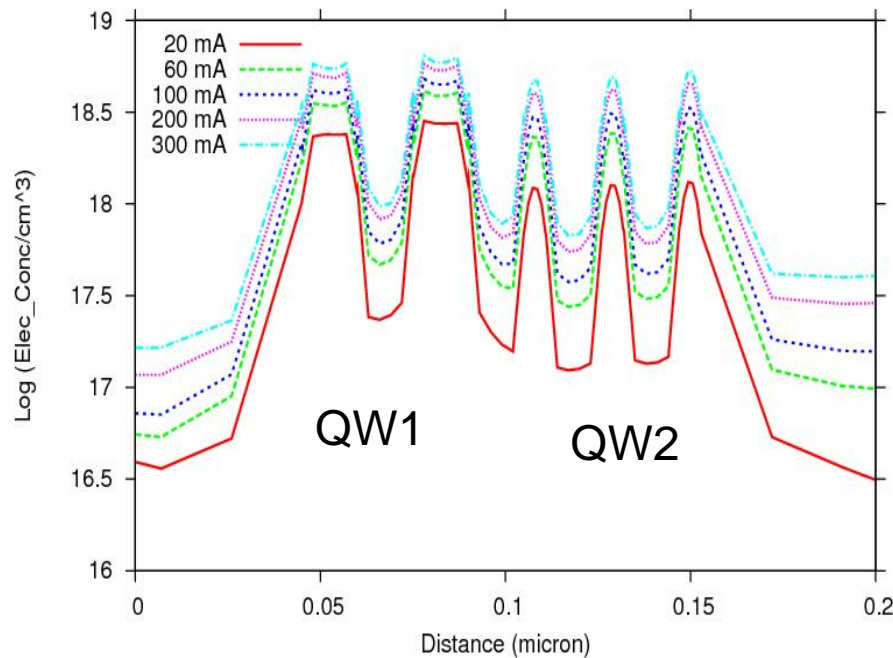


Band diagram at 0.7V



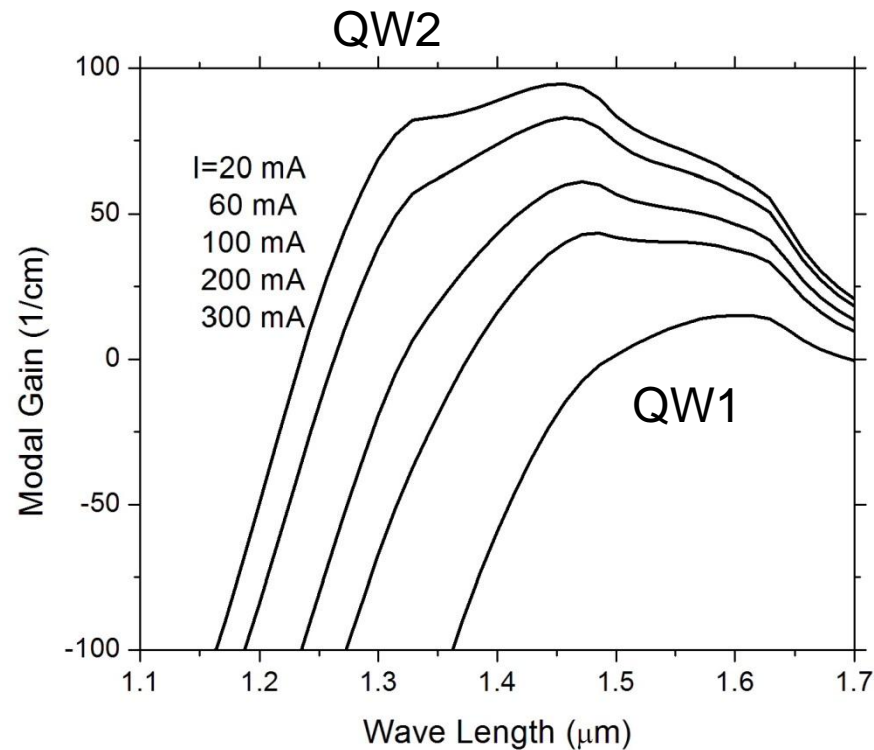
QW1: two transitions
QW2: one transition
Broad band 1.3-1.6 μm

Carrier distribution at different injections

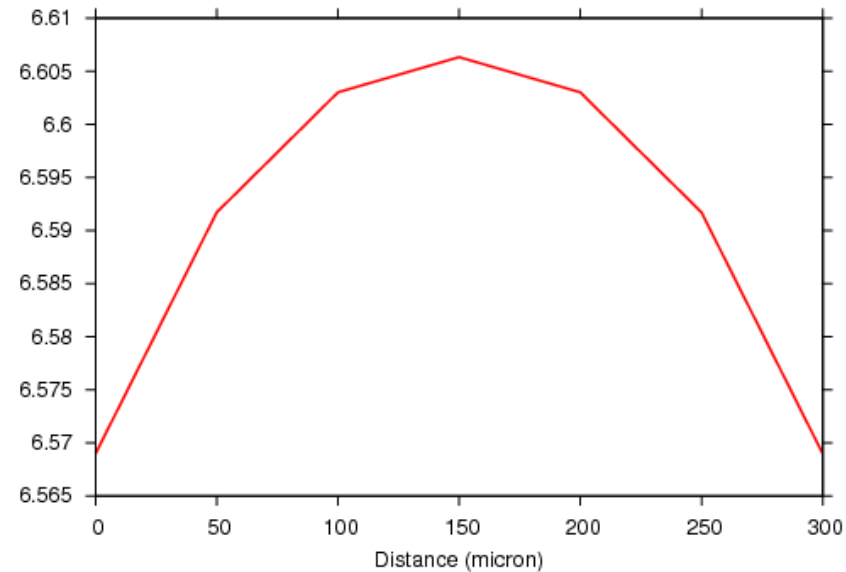
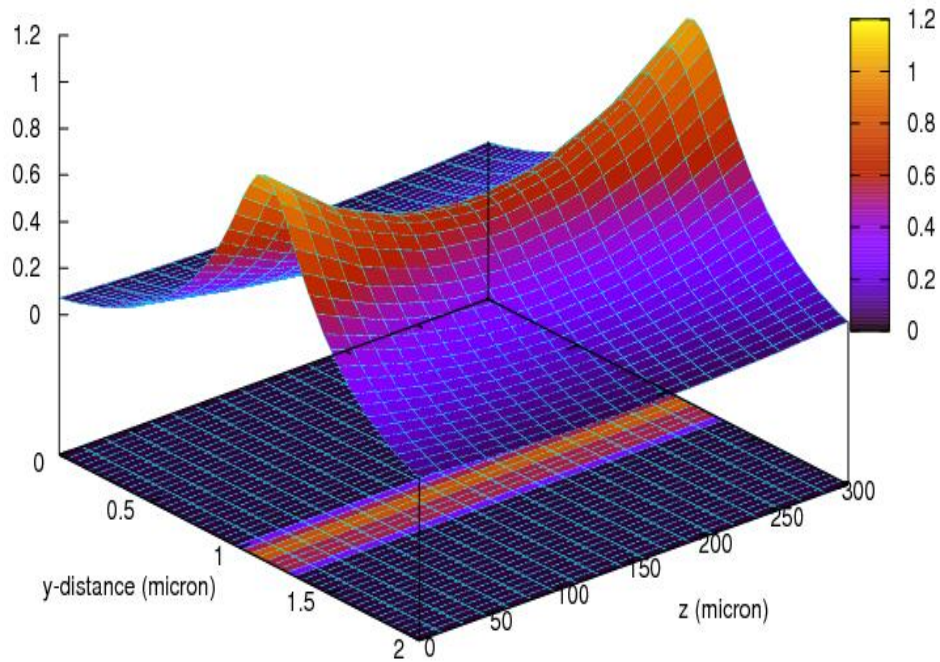


Carrier first captured in QW1,
and in QW2 at high injection

Modal gain at different injections



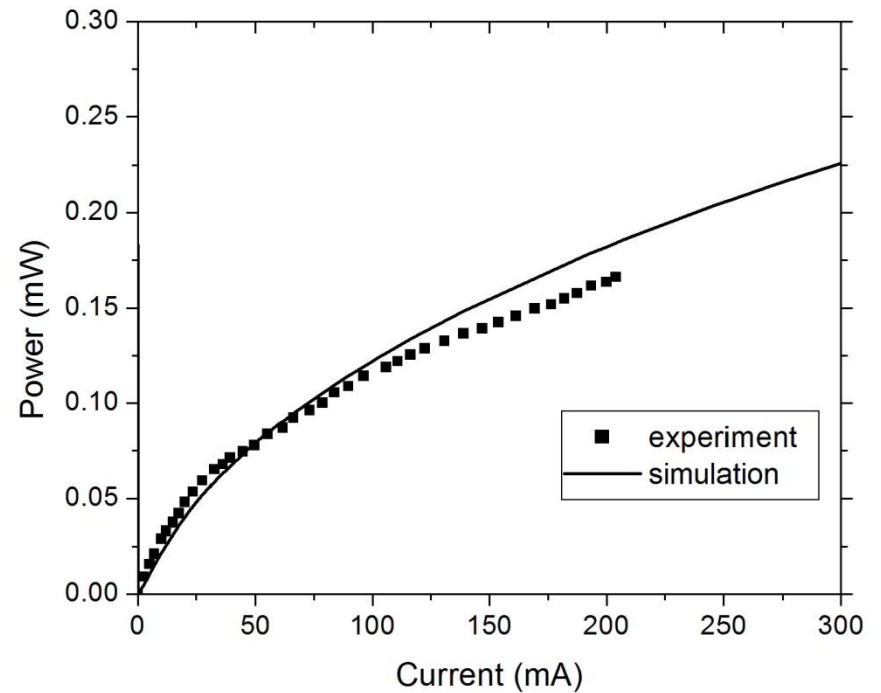
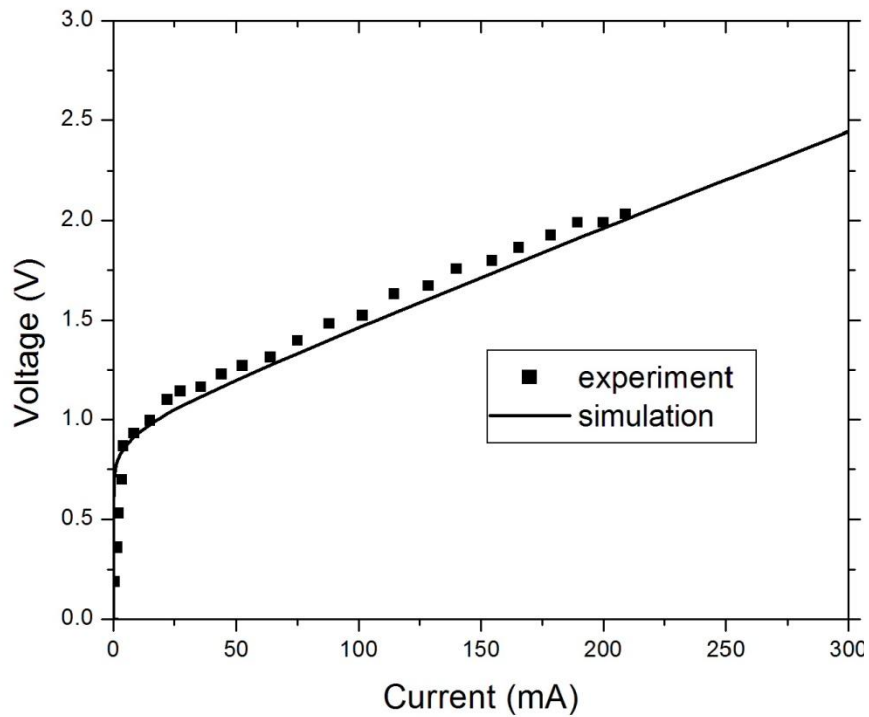
3D wave, SHB



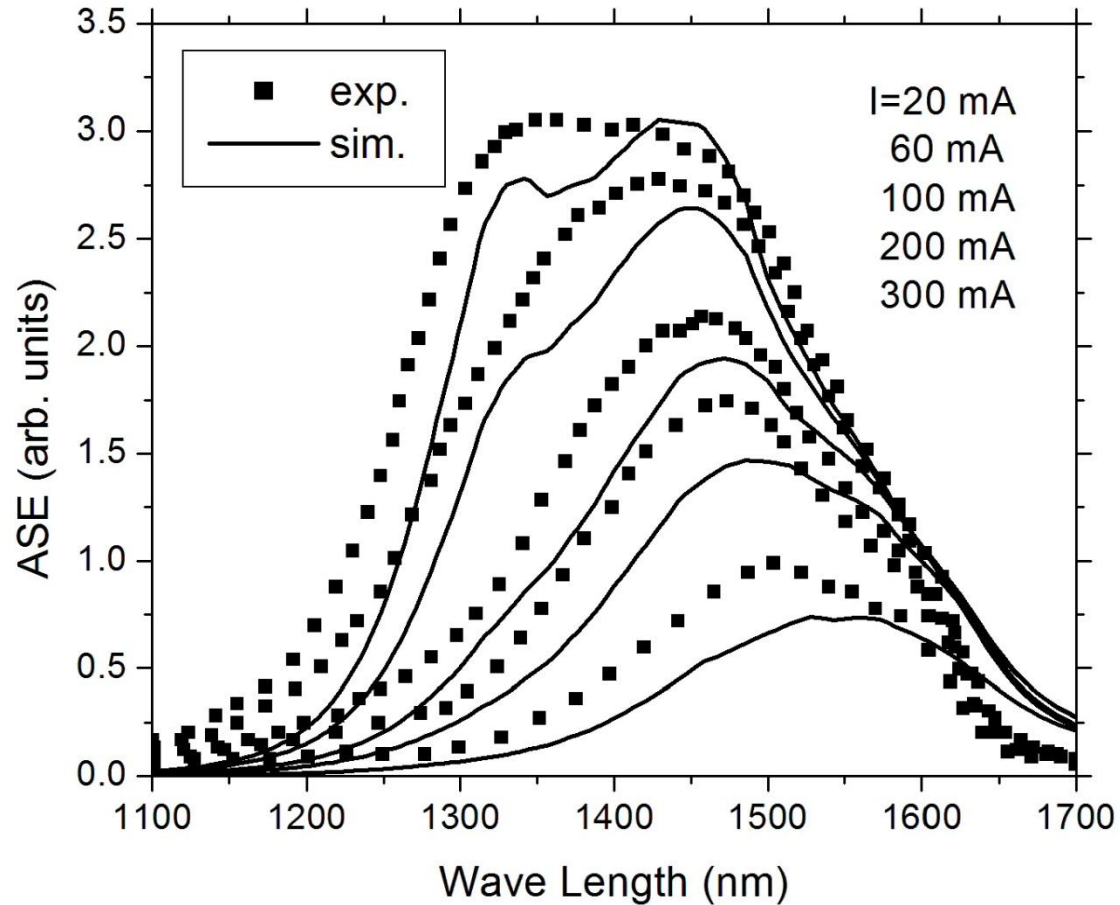
Hole density along z

Spatial hole burning is not negligible

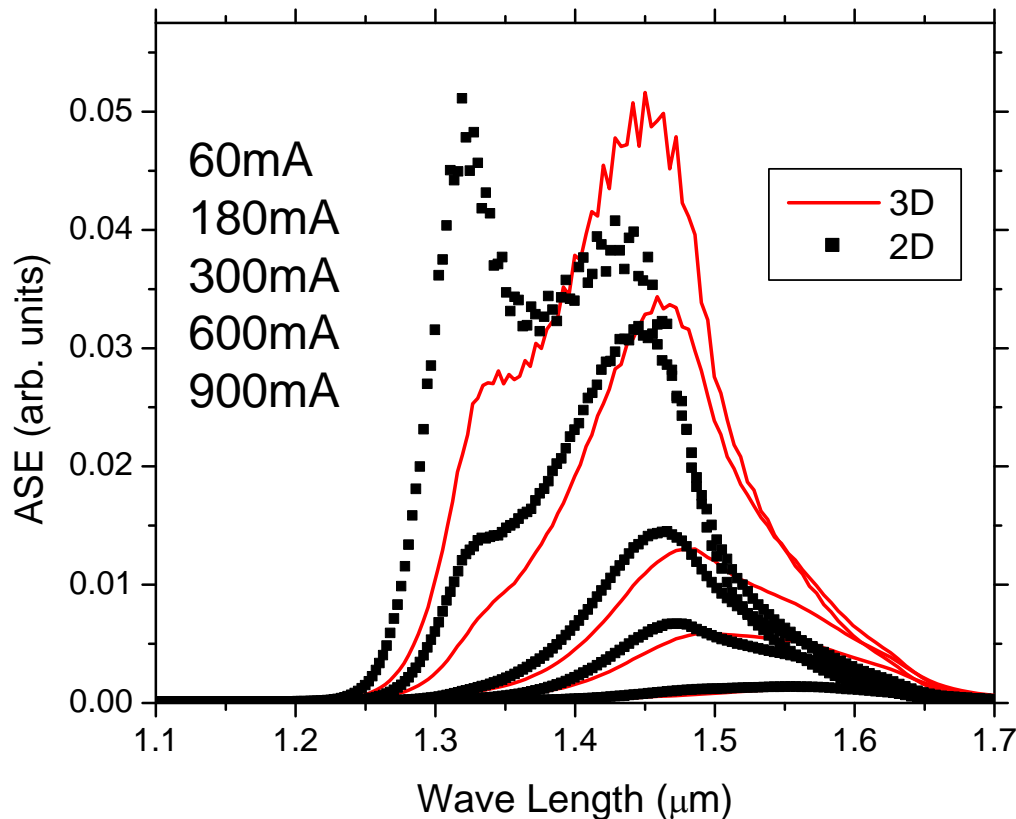
I-V and L-I curves



Amplifier spontaneous emission



3D effect on ASE



Cavity length: 900 μm
3D effect shown at higher injections

Summary

- Comprehensive model for SLED simulation is presented. 3D carrier dynamics and longitudinal SHP are included.
- Carrier distribution is important for broad-band SLED.
- SHB is not negligible at high injections
- Full 3D simulation is necessary